

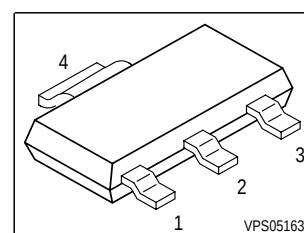
SIPMOS® Small-Signal-Transistor

Features

- N-Channel
- Enhancement mode
- Logic Level
- dv/dt rated

Product Summary

Drain source voltage	V_{DS}	30	V
Drain-Source on-state resistance	$R_{DS(on)}$	0.05	Ω
Continuous drain current	I_D	4.7	A



Type	Package	Ordering Code
BSP308	SOT-223	Q67000-S4011

Pin 1	Pin 2/4	PIN 3
G	D	S

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_A = 25\text{ °C}$ $T_A = 70\text{ °C}$	I_D	4.7 3.9	A
Pulsed drain current $T_A = 25\text{ °C}$	$I_{D\text{ puls}}$	18.8	
Reverse diode dv/dt $I_S = 4.7\text{ A}$, $V_{DS} = 20\text{ V}$, $di/dt = 200\text{ A}/\mu\text{s}$, $T_{j\text{max}} = 150\text{ °C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_A = 25\text{ °C}$	P_{tot}	1.8	W
Operating and storage temperature	T_j , T_{stg}	-55...+150	°C
IEC climatic category; DIN IEC 68-1		55/150/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point	R_{thJS}	-	-	25	K/W
SMD version, device on PCB:	R_{thJA}				K/W
@ min. footprint		-	-	110	
@ 6 cm ² cooling area ¹⁾		-	-	70	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	$V_{(BR)DSS}$	30	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 20\text{ }\mu\text{A}$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ }^{\circ}\text{C}$ $V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 125\text{ }^{\circ}\text{C}$	I_{DSS}	-	0.1	1	μA
		-	10	100	
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	10	100	nA
Drain-Source on-state resistance $V_{GS} = 4.5\text{ V}$, $I_D = 3.9\text{ A}$	$R_{DS(on)}$	-	0.05	0.075	Ω
Drain-Source on-state resistance $V_{GS} = 10\text{ V}$, $I_D = 4.7$	$R_{DS(on)}$	-	0.03	0.05	Ω

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Dynamic Characteristics

Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 3.9\text{ A}$	g_{fs}	6.1	8.8	-	S
Input capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	400	500	pF
Output capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	160	200	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	70	90	
Turn-on delay time $V_{DD} = 15\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 3.9\text{ A}$, $R_G = 15\text{ }\Omega$	$t_{d(on)}$	-	16	24	ns
Rise time $V_{DD} = 15\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 3.9\text{ A}$, $R_G = 15\text{ }\Omega$	t_r	-	30	45	
Turn-off delay time $V_{DD} = 15\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 3.9\text{ A}$, $R_G = 15\text{ }\Omega$	$t_{d(off)}$	-	16	24	
Fall time $V_{DD} = 15\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 3.9\text{ A}$, $R_G = 15\text{ }\Omega$	t_f	-	15	23	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Dynamic Characteristics

Gate to source charge $V_{DD} = 24\text{ V}$, $I_D = 4.7\text{ A}$	Q_{gs}	-	1.9	2.9	nC
Gate to drain charge $V_{DD} = 24\text{ V}$, $I_D = 4.7\text{ A}$	Q_{gd}	-	5.4	8.1	
Gate charge total $V_{DD} = 24\text{ V}$, $I_D = 4.7\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$	Q_g	-	14.5	22	
Gate plateau voltage $V_{DD} = 24\text{ V}$, $I_D = 4.7\text{ A}$	$V_{(plateau)}$	-	3.1	-	V

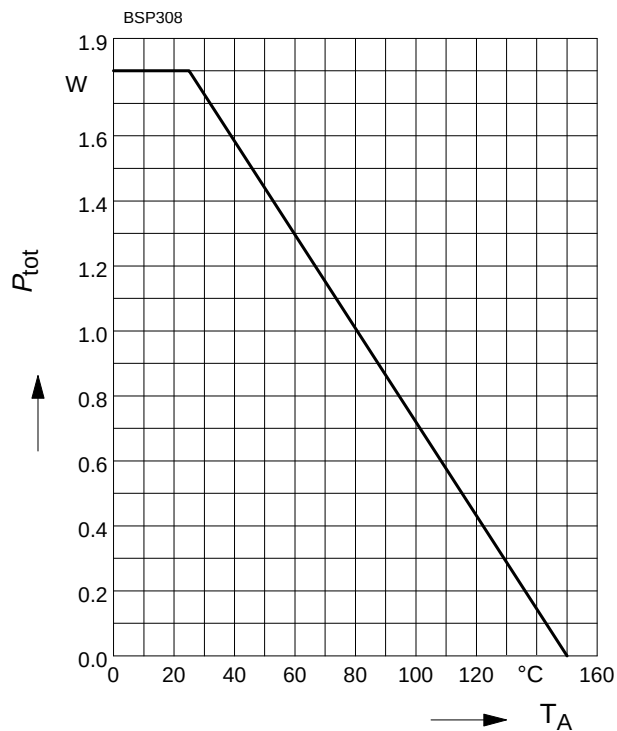
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Reverse Diode

Inverse diode continuous forward current $T_A = 25\text{ °C}$	I_S	-	-	4.7	A
Inverse diode direct current,pulsed $T_A = 25\text{ °C}$	I_{SM}	-	-	18.8	
Inverse diode forward voltage $V_{GS} = 0\text{ V}$, $I_F = 4.7\text{ A}$	V_{SD}	-	0.84	1.1	V
Reverse recovery time $V_R = 15\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	38.4	57.6	ns
Reverse recovery charge $V_R = 15\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	22.3	33.5	nC

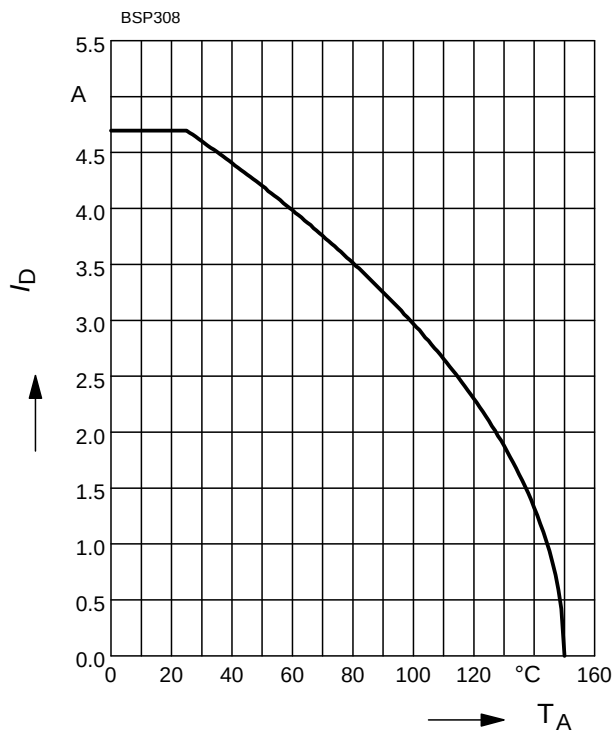
Power Dissipation

$$P_{\text{tot}} = f(T_A)$$



Drain current

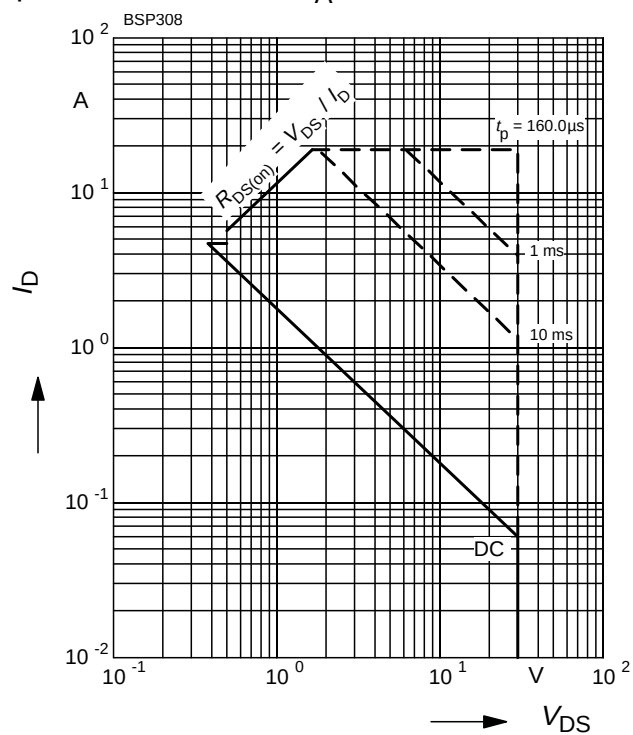
$$I_D = f(T_A)$$



Safe operating area

$$I_D = f(V_{DS})$$

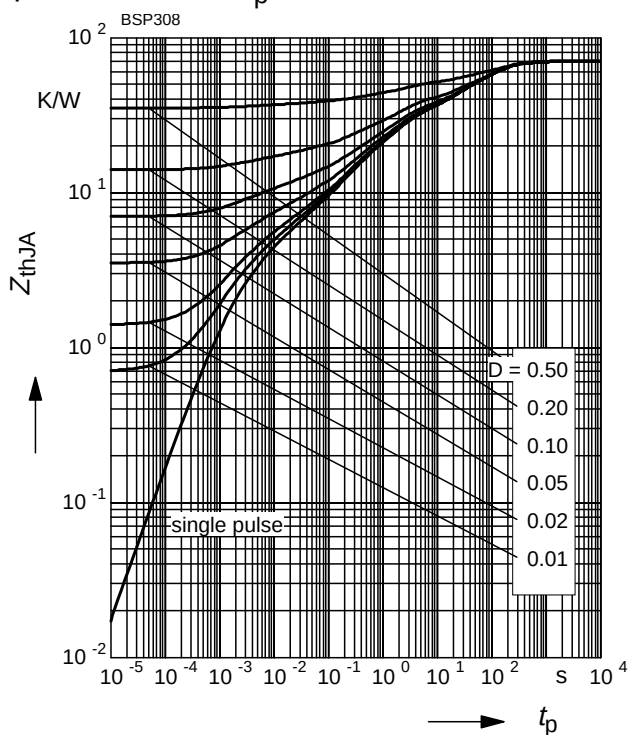
parameter : $D = 0$, $T_A = 25^\circ\text{C}$



Transient thermal impedance

$$Z_{\text{thJA}} = f(t_p)$$

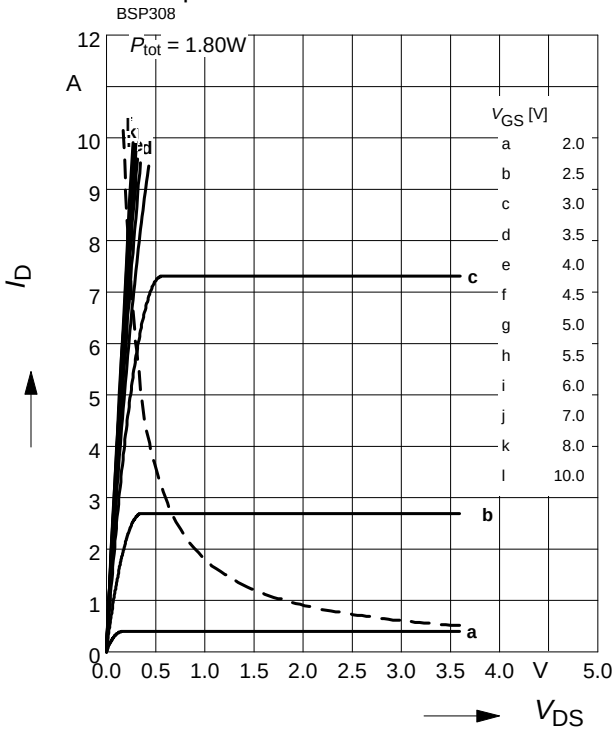
parameter : $D = t_p / T$



Typ. output characteristics

$$I_D = f(V_{DS})$$

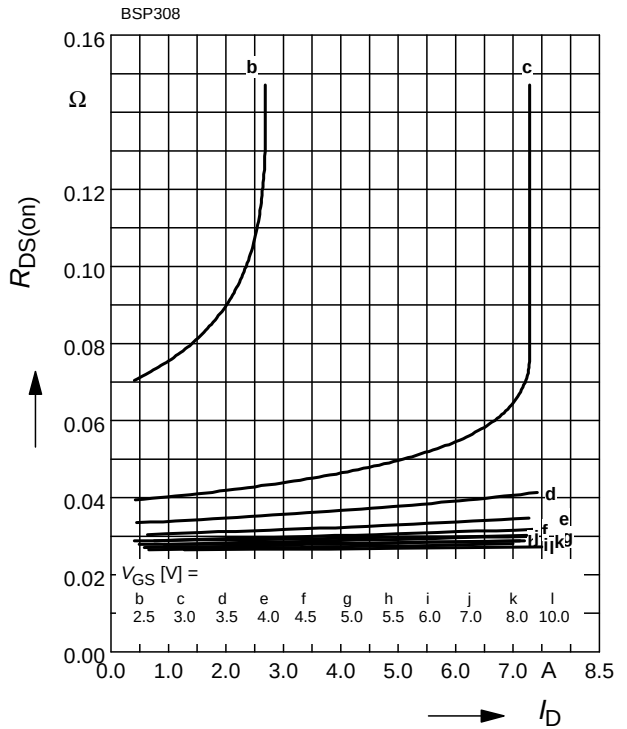
parameter: $t_p = 80 \mu s$



Typ. drain-source-on-resistance

$$R_{DS(on)} = f(I_D)$$

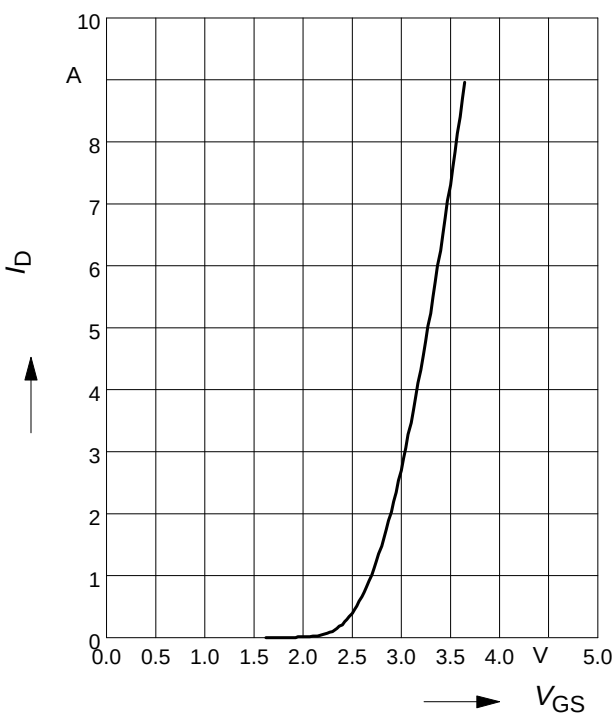
parameter: V_{GS}



Typ. transfer characteristics $I_D = f(V_{GS})$

$$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

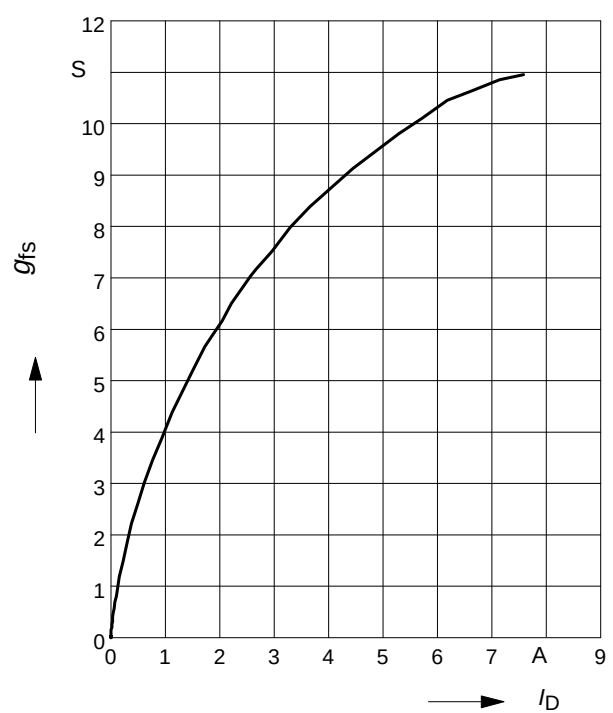
parameter: $t_p = 80 \mu s$



Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ C$$

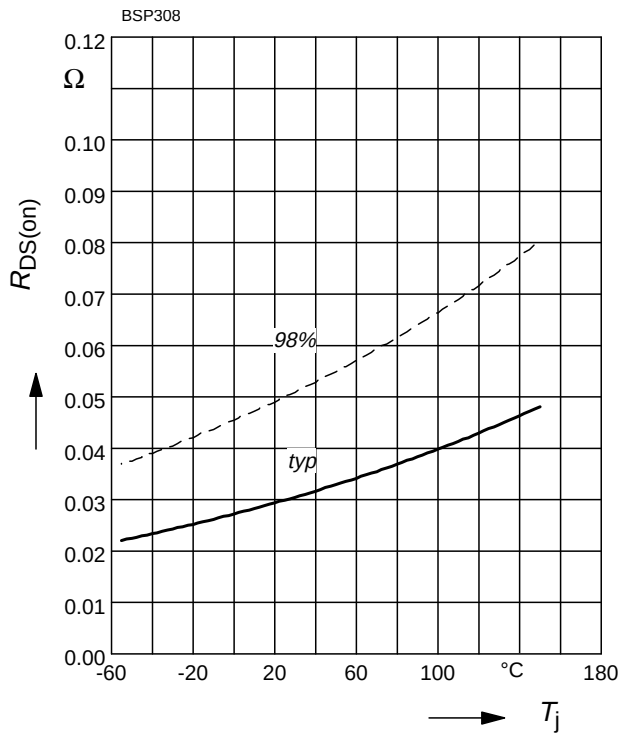
parameter: g_{fs}



Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

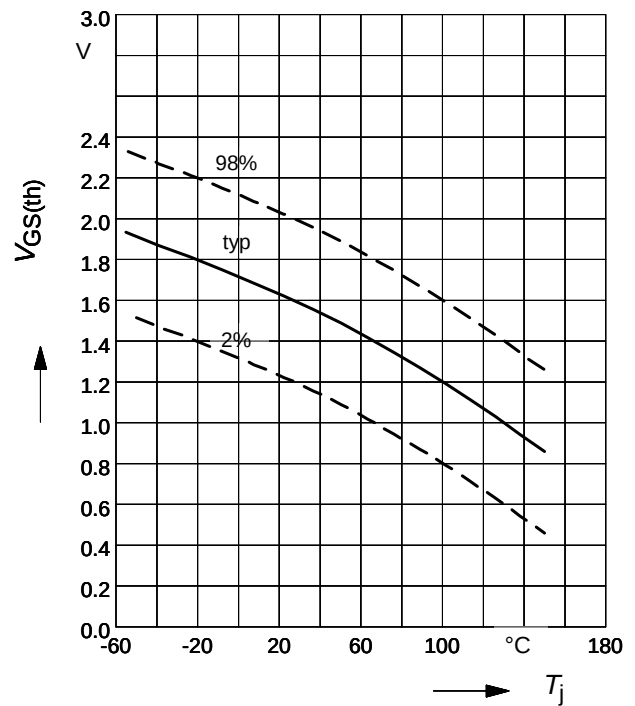
parameter: $I_D = 4.7$, $V_{GS} = 10$ V



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

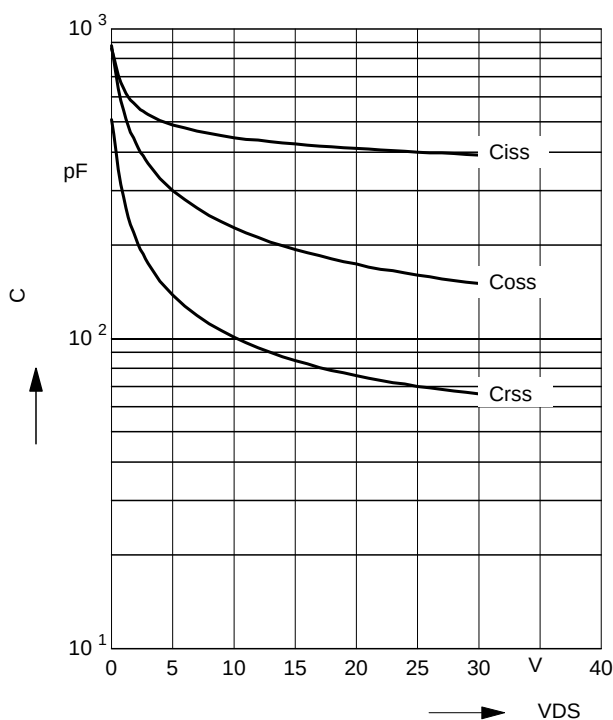
parameter: $V_{GS} = V_{DS}$, $I_D = 20$ μA



Typ. capacitances

$$C = f(V_{DS})$$

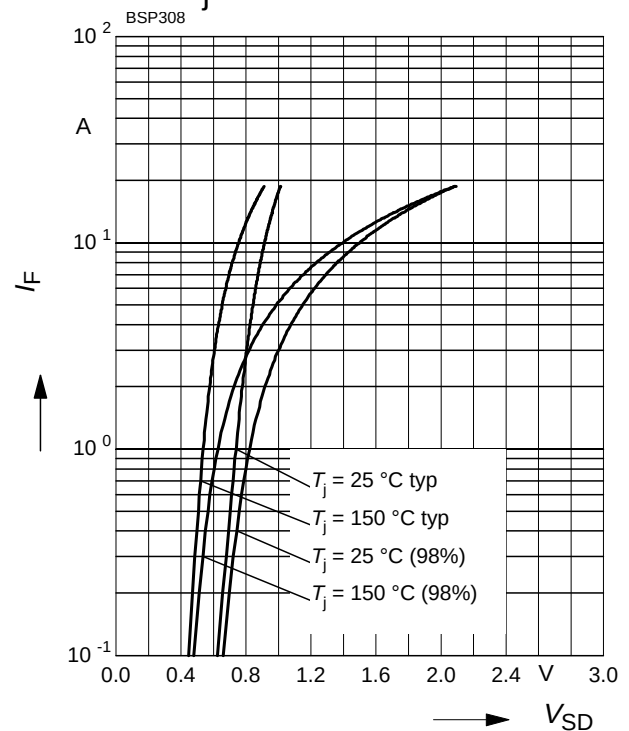
parameter: $V_{GS} = 0$ V, $f = 1$ MHz



Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

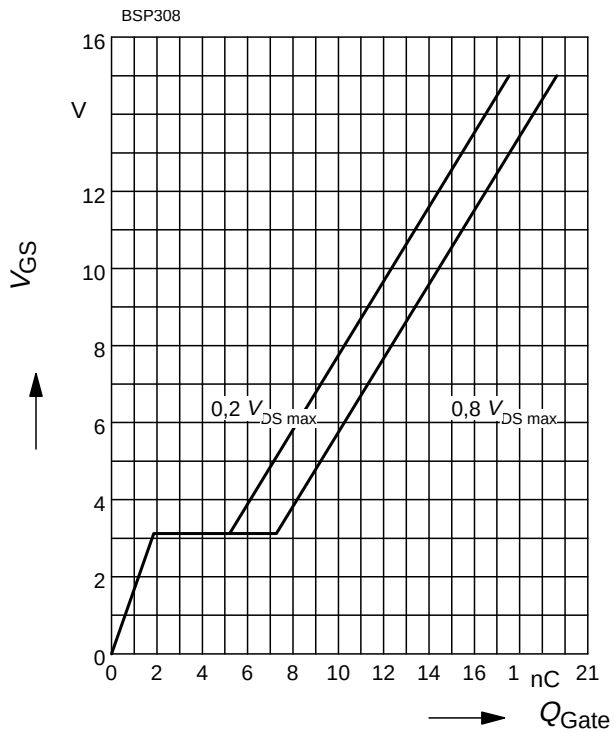
parameter: T_j , $t_p = 80$ μs



Typ. gate charge

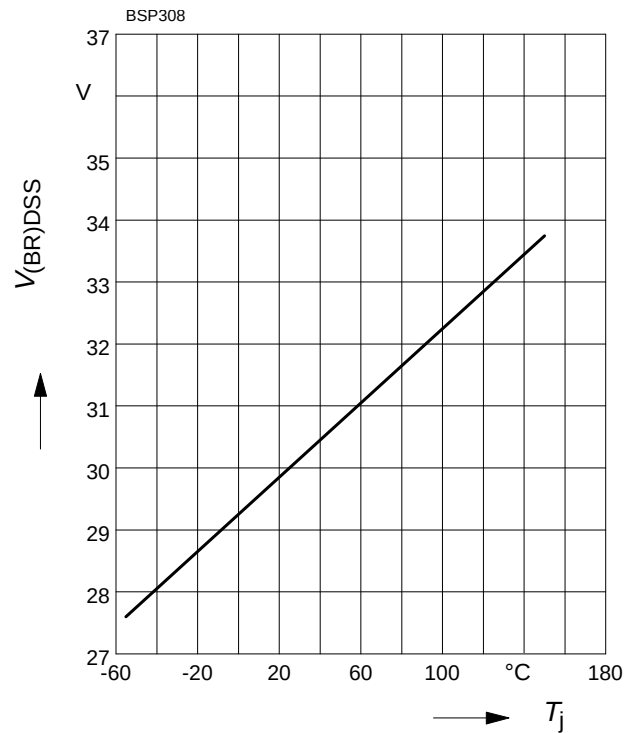
$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = 4.7$ A pulsed



Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$



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